

N-Channel Reduced Q_g , Fast Switching MOSFET

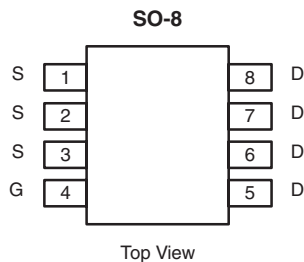
| PRODUCT SUMMARY | | |
|-----------------|---------------------------|-----------|
| V_{DS} (V) | $R_{DS(on)}$ (Ω) | I_D (A) |
| 60 | 0.022 at $V_{GS} = 10$ V | 8.5 |
| | 0.031 at $V_{GS} = 4.5$ V | 7.2 |

FEATURES

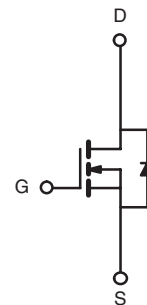
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFETs
- 175 °C Maximum Junction Temperature
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available



Ordering Information: Si4850EY-T1-E3 (Lead (Pb)-free)
Si4850EY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted | | | | | |
|--|----------------|---------------|--------------|------|---|
| Parameter | Symbol | 10 s | Steady State | Unit | |
| Drain-Source Voltage | V_{DS} | 60 | | V | |
| Gate-Source Voltage | V_{GS} | ± 20 | | | |
| Continuous Drain Current ($T_J = 175$ °C) ^a | I_D | $T_A = 25$ °C | 8.5 | 6.0 | A |
| | | $T_A = 70$ °C | 7.1 | 5.0 | |
| Pulsed Drain Current | I_{DM} | 40 | | | |
| Avalanche Current | I_{AS} | 15 | | | |
| Single Pulse Avalanche Energy | E_{AS} | 11 | | mJ | |
| Maximum Power Dissipation ^a | P_D | $T_A = 25$ °C | 3.3 | 1.7 | W |
| | | $T_A = 70$ °C | 2.3 | 1.2 | |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | - 55 to 175 | | °C | |

| THERMAL RESISTANCE RATINGS | | | | | |
|--|---------------|------------|---------|---------|------|
| Parameter | | Symbol | Typical | Maximum | Unit |
| Maximum Junction-to-Ambient ^a | $t \leq 10$ s | R_{thJA} | 36 | 45 | °C/W |
| | Steady State | | 75 | 90 | |
| Maximum Junction-to-Foot (Drain) | Steady State | R_{thJF} | 17 | 20 | |

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

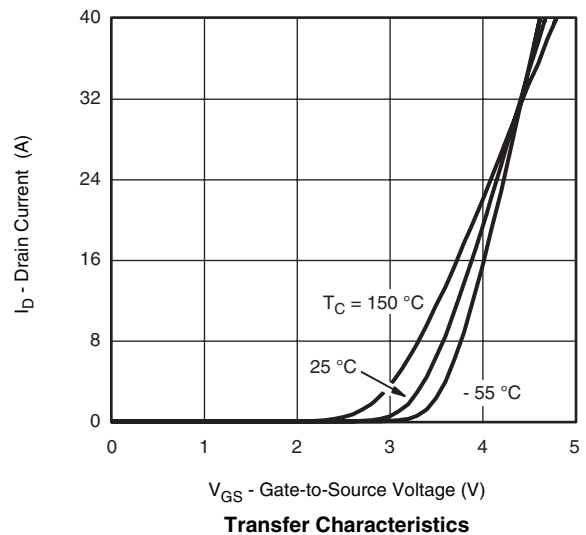
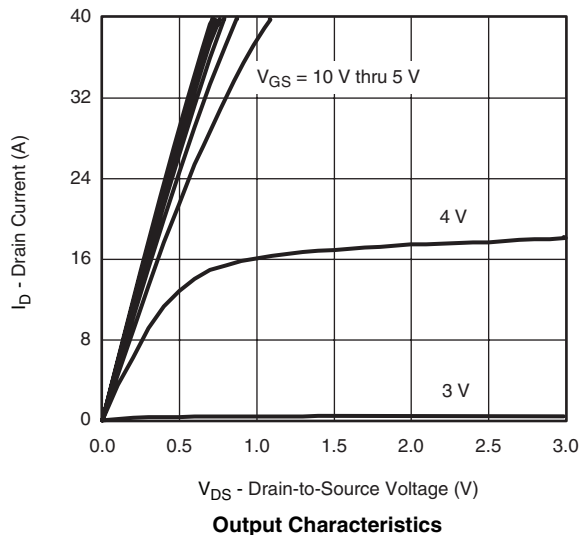
| SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted | | | | | | |
|--|--------------|--|------|-------|-----------|---------------|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | 60 | | | V |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | 1 | | 3 | |
| Gate-Body Leakage | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$ | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$ | | | 1 | μA |
| | | $V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$ | | | 20 | |
| On-State Drain Current ^a | $I_{D(on)}$ | $V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$ | 40 | | | A |
| Drain-Source On-State Resistance ^a | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}, I_D = 6.0\text{ A}$ | | 0.018 | 0.022 | Ω |
| | | $V_{GS} = 10\text{ V}, I_D = 6.0\text{ A}, T_J = 125\text{ }^\circ\text{C}$ | | 0.031 | 0.037 | |
| | | $V_{GS} = 10\text{ V}, I_D = 6.0\text{ A}, T_J = 175\text{ }^\circ\text{C}$ | | 0.039 | 0.047 | |
| | | $V_{GS} = 4.5\text{ V}, I_D = 5.1\text{ A}$ | | 0.025 | 0.031 | |
| Forward Transconductance ^a | g_{fs} | $V_{DS} = 15\text{ V}, I_D = 6.0\text{ A}$ | | 25 | | S |
| Diode Forward Voltage ^a | V_{SD} | $I_S = 1.7\text{ A}, V_{GS} = 0\text{ V}$ | | 0.8 | 1.2 | V |
| Dynamic^b | | | | | | |
| Total Gate Charge | Q_g | $V_{DS} = 30\text{ V}, V_{GS} = 10\text{ V}, I_D = 6.0\text{ A}$ | | 18 | 27 | nC |
| Gate-Source Charge | Q_{gs} | | | 3.4 | | |
| Gate-Drain Charge | Q_{gd} | | | 5.3 | | |
| Gate Resistance | R_g | $V_{GS} = 0.1\text{ V}, f = 5\text{ MHz}$ | 0.5 | 1.4 | 2.4 | Ω |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = 30\text{ V}, R_L = 30\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 6\text{ }\Omega$ | | 10 | 20 | ns |
| Rise Time | t_r | | | 10 | 20 | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 25 | 50 | |
| Fall Time | t_f | | | 12 | 24 | |
| Source-Drain Reverse Recovery Time | t_{rr} | $I_F = 1.7\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$ | | 50 | 80 | |

Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless otherwise noted



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



On-Resistance vs. Drain Current



Capacitance



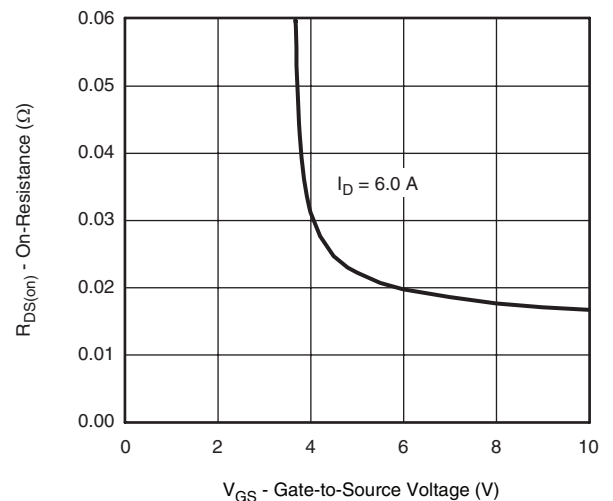
Gate Charge



On-Resistance vs. Junction Temperature

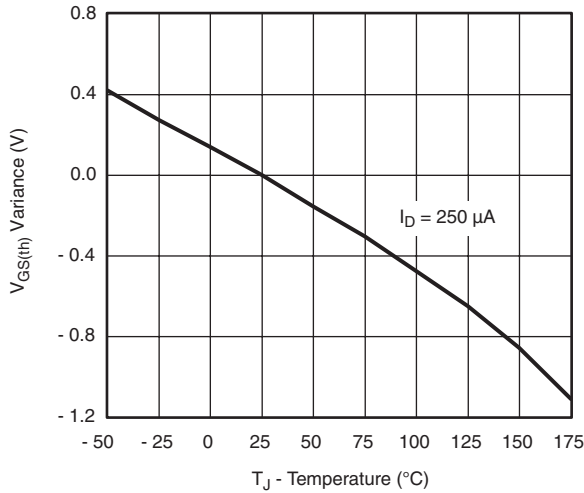


Source-Drain Diode Forward Voltage

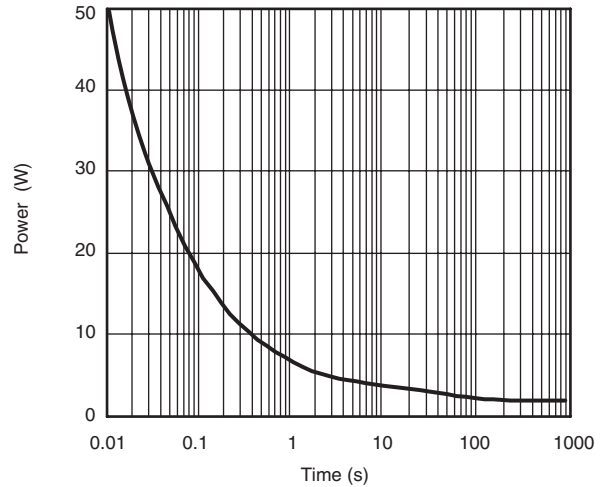


On-Resistance vs. Gate-to-Source Voltage

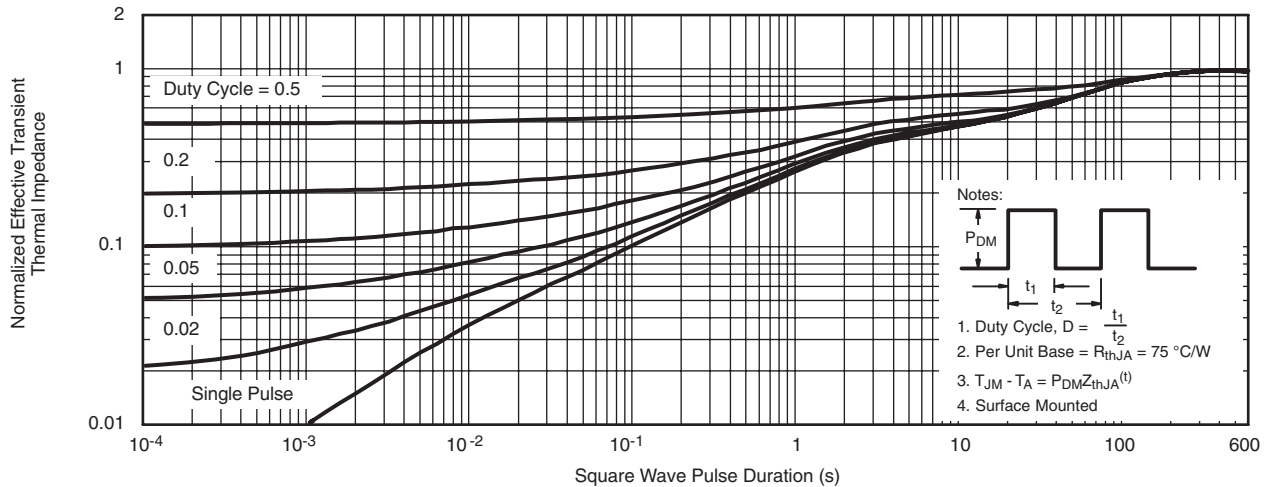
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



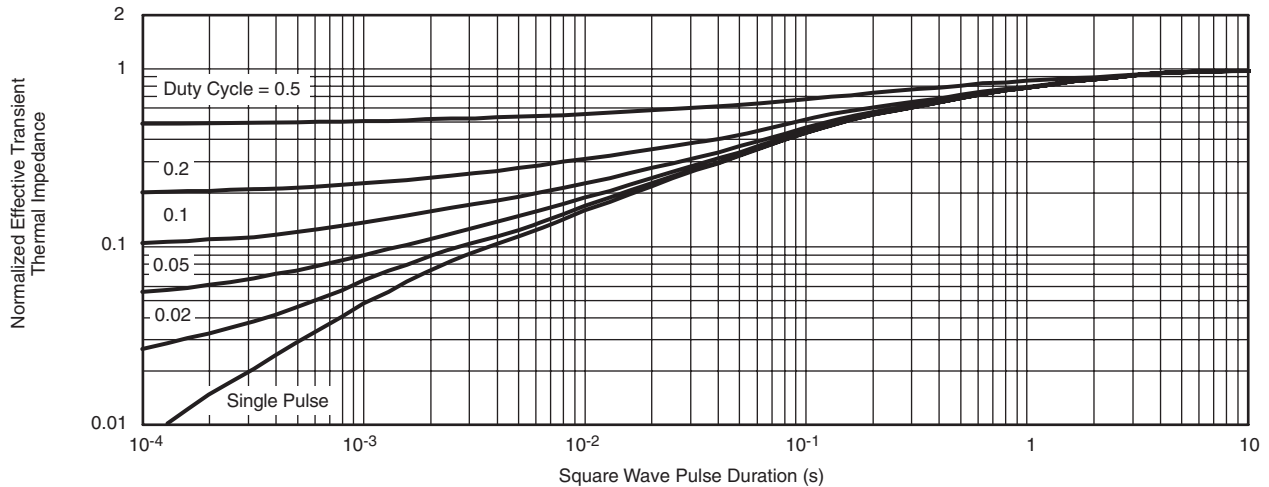
Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



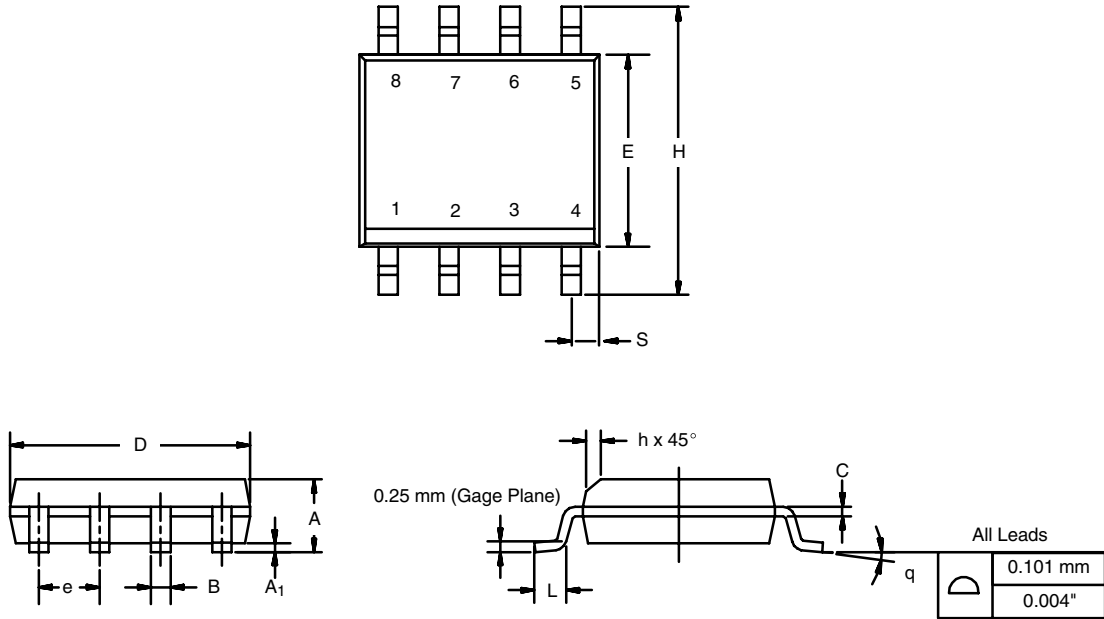
Normalized Thermal Transient Impedance, Junction-to-Foot

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SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



| DIM | MILLIMETERS | | INCHES | |
|---|-------------|------|-----------|-------|
| | Min | Max | Min | Max |
| A | 1.35 | 1.75 | 0.053 | 0.069 |
| A ₁ | 0.10 | 0.20 | 0.004 | 0.008 |
| B | 0.35 | 0.51 | 0.014 | 0.020 |
| C | 0.19 | 0.25 | 0.0075 | 0.010 |
| D | 4.80 | 5.00 | 0.189 | 0.196 |
| E | 3.80 | 4.00 | 0.150 | 0.157 |
| e | 1.27 BSC | | 0.050 BSC | |
| H | 5.80 | 6.20 | 0.228 | 0.244 |
| h | 0.25 | 0.50 | 0.010 | 0.020 |
| L | 0.50 | 0.93 | 0.020 | 0.037 |
| q | 0° | 8° | 0° | 8° |
| S | 0.44 | 0.64 | 0.018 | 0.026 |
| ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498 | | | | |

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

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